CPH6636R

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N-Channel Power MOSFET 24V, 6A, 20mΩ, Dual CPH6 Common Drain

Features

- Low On-resistance
- Best suited for LiB charging and discharging switch
- With a built-in gate resistor
- Protection diode in

- 2.5V drive
- Common-drain type
- Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	VDSS		24	V
Gate to Source Voltage	VGSS		±12	V
Drain Current (DC)	ID		6	Α
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	36	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate(900mm ² ×0.8mm) 1unit	0.9	W
Total Dissipation	PT	When mounted on ceramic substrate(900mm²×0.8mm)	1.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		- 55 to +150	°C

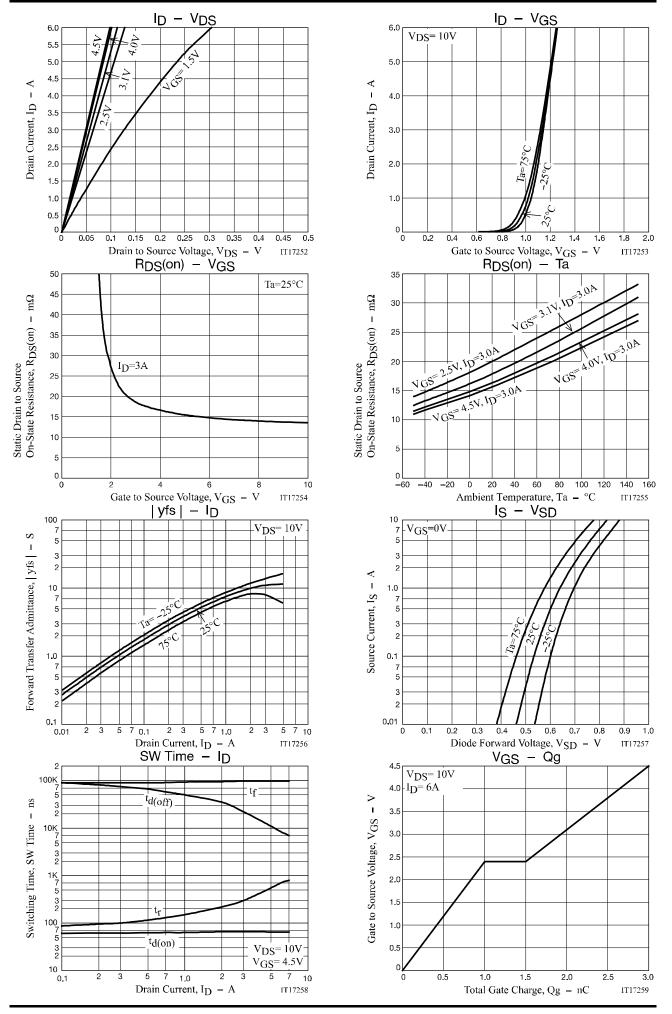
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Electrical Characteristics at Ta = 25°C

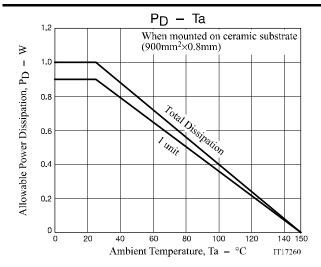
	Symbol	2	Ratings			
Parameter		Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	24			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±1	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	0.5		1.3	٧
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =3A		11		S
	R _{DS} (on)1	I _D =3A, V _{GS} =4.5V	12.8	16	20	mΩ
Chatia Basia da Cassas On Chata Basiatas	R _{DS} (on)2	I _D =3A, V _{GS} =4.0V	13.3	16.7	21.7	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)3	I _D =3A, V _{GS} =3.1V	14.6	18.3	25.6	mΩ
	R _{DS} (on)4	I _D =3A, V _{GS} =2.5V	16.4	20.5	28.7	mΩ
Turn-ON Delay Time	t _d (on)			65		ns
Rise Time	t _r	0		300		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		22000		ns
Fall Time	tf			98000		ns
Total Gate Charge	Qg			3		nC
Gate to Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =6A		1		nC
Gate to Drain "Miller" Charge	Qgd]		0.5		nC
Diode Forward Voltage	V _{SD}	I _S =6A, V _{GS} =0V		0.78	1.2	٧

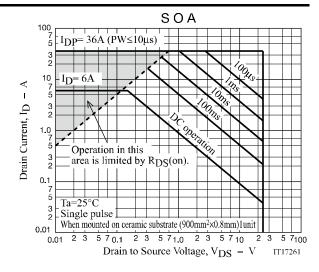
ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.



CPH6636R





Package Dimensions

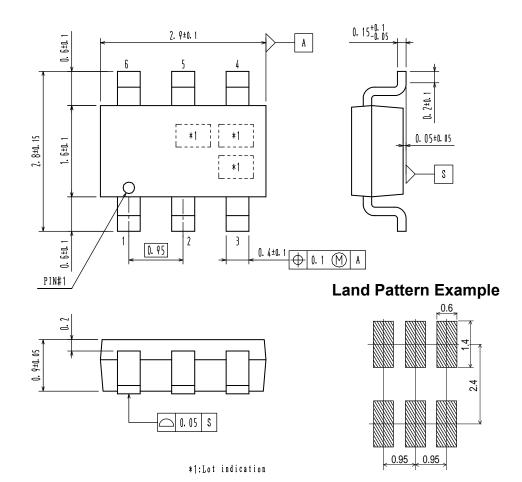
CPH6636R-TL-W

CPH6

CASE 318BD ISSUE O

Unit: mm

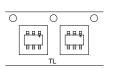
- 1: Source1
- 2: Drain
- 3: Source2
- 4: Gate2
- 5: Drain
- 6: Gate1



Ordering & Package Information

Device	Package	Shipping	note
CPH6636R-TL-W	CPH6, SC-74 SOT-26, SOT-457	3,000 pcs. / reel	Pb-Free And Halogen Free

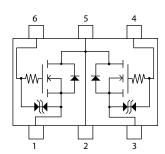
Packing Type:TL



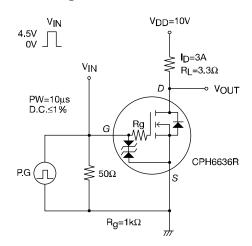
Marking



Electrical Connection



Switching Time Test Circuit



CPH6636R

Note on usage: Since the CPH6636R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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